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LED980-66-60

TECHNICAL DATA



High Power LED Array, 60 chips

GaAs

LED980-66-60 is a wide viewing and extremely high output power illuminator assembled with a total of 60 high efficiency GaAs diode chips, mounted on a metal stem TO-66 with AIN ceramics and covered with double coated clear silicone and epoxy resin.

These devices are designed for high current operation with proper heat sinking to improver thermal conductive efficiency.

Specifications

Structure: GaAs. 60 LED chips Peak Wavelength: typ. 980 nm

Optical Output Power: typ. 150 mW

Package: TO-66 stem with AIN,

epoxy resin

Absolute Maximum Ratings ($T_C=25$ °C)

Item	Symbol	Value	Unit
Power Dissipation	P_{D}	8.2	W
Forward Current	I_F	800	mΑ
Pulsed Forward Current *1	I_{FP}	3	Α
Reverse Voltage	V_R	30	V
Operating Temperature	T_{opr}	-30 +80	ç
Storage Temperature	T_{stg}	-30 +110	ç
Soldering Temperature *2	T_{sol}	265	°C

 $^{^{*1}}$ duty = 1%, pulse width = 1 μ s

24.38 $2 - \emptyset 3.58$ ① Anode ② Cathode 0 (Unit: mm)



Electro-Optical Characteristics

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Total Radiated Power	Po	$I_F = 600 \text{ mA}$	-	150	-	mW
Radiant Intensity	Ι _Ε	$I_F = 600 \text{ mA}$	-	-	-	mW/sr
Forward Voltage	V _F	$I_F = 600 \text{ mA}$	-	6.3	-	V
Peak Wavelength	λ_{P}	$I_F = 600 \text{ mA}$	975	985	995	nm
Half Width	Δλ	$I_F = 600 \text{ mA}$	-	45	-	nm
Viewing Half Angle	Θ _{1/2}	$I_{\rm F}$ = 600 mA	-	±60	-	deg.

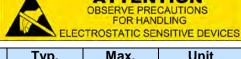
Heat Sink is required, LED is required to keep less than 60°C

Notes





The above specifications are for reference purpose only and subjected to change without prior notice.



^{*2} must be completed within 3 seconds